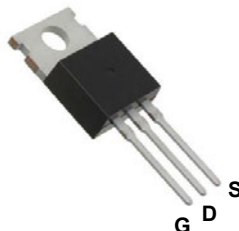
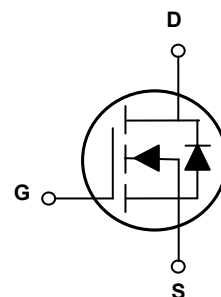


Main Product Characteristics

$V_{(BR)DSS}$	600V
$R_{DS(ON)}$	0.57 Ω (Max.)
I_D	7A



TO-220



Schematic Diagram

Features and Benefits

- Optimized the cell structure
- Low on-resistance and low gate charge
- Featuring low switching and drive losses
- Fast switching and reverse body recovery
- High ruggedness and robustness

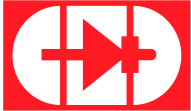


Description

The GSFH60R570 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supplies and a wide variety of other applications.

Absolute Maximum Ratings (T_C=25°C unless otherwise specified)

Parameter	Symbol	Max.	Unit
Drain-Source Voltage	V_{DS}	600	V
Gate-Source Voltage	V_{GS}	±30	V
Drain Current-Continuous, at Steady-State, (T _C =25°C)	I_D	7	A
Drain Current-Continuous, at Steady-State, (T _C =100°C)		4.4	
Drain Current-Pulsed	I_{DM}	28	A
Single Pulse Avalanche Energy ¹	E_{AS}	221	mJ
Power Dissipation (T _C =25°C)	P_D	60	W
		0.48	W/°C
Body Diode Reverse Voltage Slope ²	dv/dt	50	V/ns
MOS dv/dt Ruggedness ³	dv/dt	100	V/ns
Junction-to-Ambient (PCB Mounted, Steady-State)	$R_{\theta JA}$	62	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.08	°C/W
Operating Junction Temperature Range	T_J	-55 To +150	°C
Storage Temperature Range	T_{STG}	-55 To +150	°C


Electrical Characteristics ($T_C=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
On / Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	600	-	-	V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=600V, V_{GS}=0V$	-	-	200	nA
Gate-Source Forward Current	I_{GSS}	$V_{GS}=\pm 30V, V_{DS}=0V$	-	-	± 100	nA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=3.5A, T_J=25^\circ\text{C}$	-	0.47	0.57	Ω
		$V_{GS}=10V, I_D=3.5A, T_J=125^\circ\text{C}$	-	0.95	-	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	2.0	-	4.0	V
Dynamic and Switching Characteristics						
Total Gate Charge ^{4,5}	Q_g	$V_{DD}=480V, I_D=7A, V_{GS}=10V$	-	19	-	nC
Gate-Source Charge ^{4,5}	Q_{gs}		-	5.1	-	
Gate-Drain ("Miller") Charge ^{4,5}	Q_{gd}		-	8.6	-	
Turn-On Delay Time ^{4,5}	$t_{d(on)}$	$V_{DD}=300V, R_G=25\Omega, V_{GS}=10V, I_D=7A$	-	20	-	nS
Rise Time ^{4,5}	t_r		-	40	-	
Turn-Off Delay Time ^{4,5}	$t_{d(off)}$		-	91	-	
Fall Time ^{4,5}	t_f		-	38	-	
Input Capacitance	C_{iss}	$V_{DS}=100V, V_{GS}=0V, F=1\text{MHz}$	-	602	-	pF
Output Capacitance	C_{oss}		-	25	-	
Reverse Transfer Capacitance	C_{rss}		-	0.8	-	
Gate Resistance	R_g	$F=1\text{MHz}$	-	4.7	-	Ω
Drain-Source Diode Characteristics and Maximum Ratings						
Continuous Source Current (Body Diode)	I_S	$T_C=25^\circ\text{C}$, MOSFET symbol showing the integral reverse p-n junction diode	-	-	7	A
Pulsed Source Current	I_{SM}		-	-	28	A
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=7A$	-	-	1.4	V
Reverse Recovery Time ³	t_{rr}	$V_{GS}=0V, I_F=7A, dI_F/dt=100A/\mu s$	-	240	-	nS
Reverse Recovery Charge ³	Q_{rr}		-	2.4	-	μC

Note:

- $L=79\text{mH}, I_{AS}=2.2A, V_{DD}=100V$, starting temperature $T_J=25^\circ\text{C}$.
- $V_{DS}=0-400V, I_{SD}\leq 20A, T_J=25^\circ\text{C}$.
- $V_{DS}=0-480V$.
- Pulse test : pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- Essentially independent of operating temperature.

Typical Electrical and Thermal Characteristic Curves

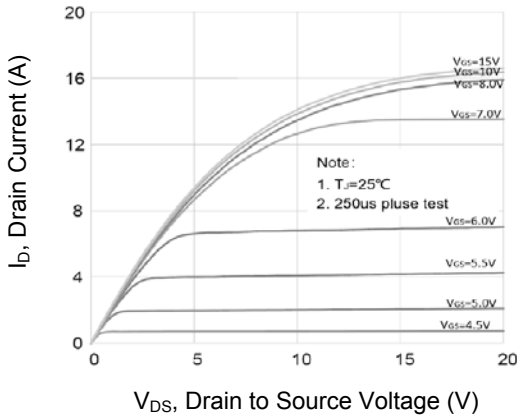


Figure 1. Output Characteristics

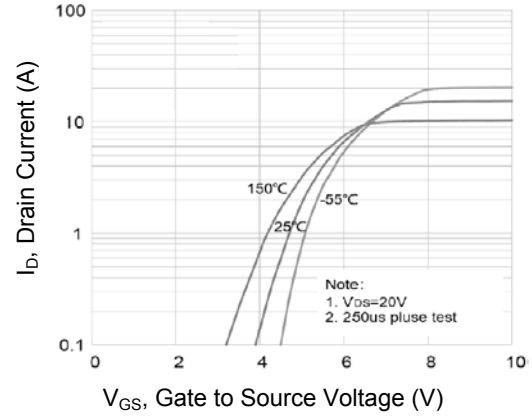


Figure 2. Transfer Characteristics

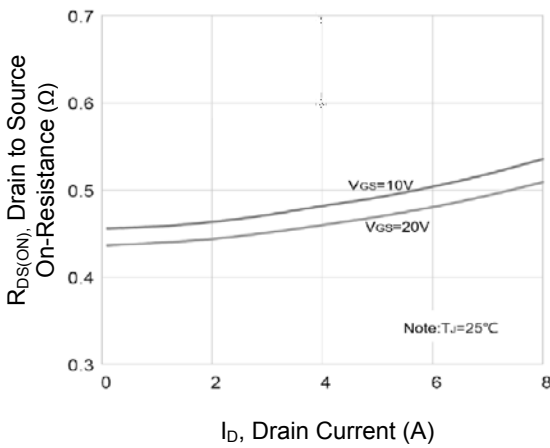


Figure 3. $R_{DS(ON)}$ vs. Drain Current

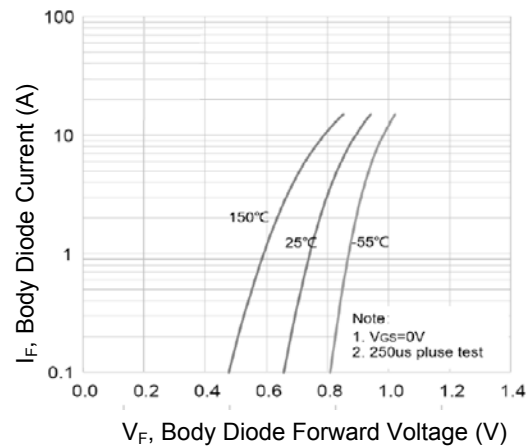


Figure 4. Body Diode Characteristics

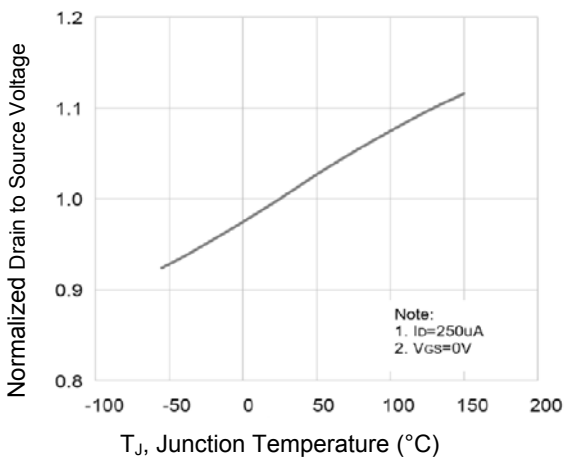


Figure 5. Normalized BV_{DSS} vs. T_J

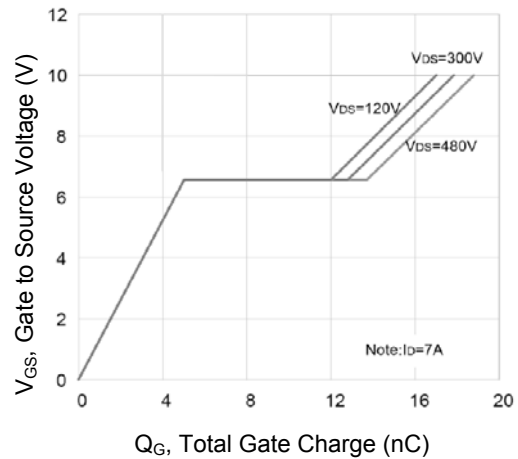


Figure 6. Gate Charge

Typical Electrical and Thermal Characteristic Curves

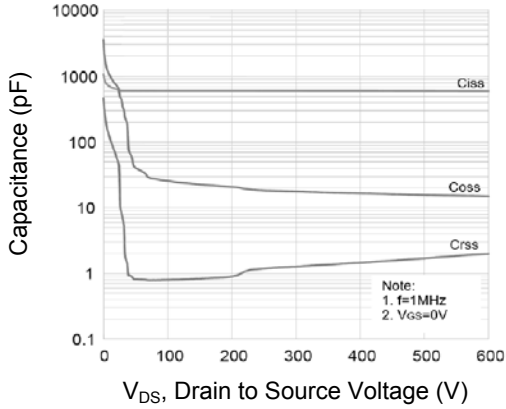


Figure 7. Capacitance Characteristics

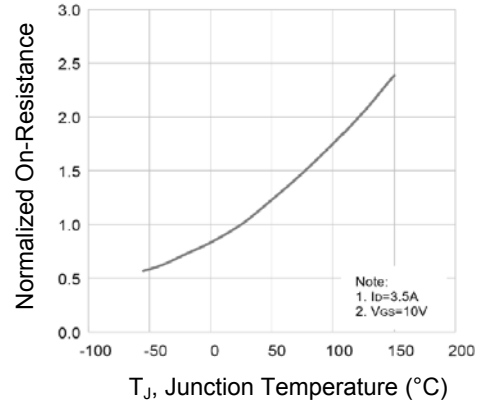


Figure 8. Normalized $R_{DS(ON)}$ vs. T_J

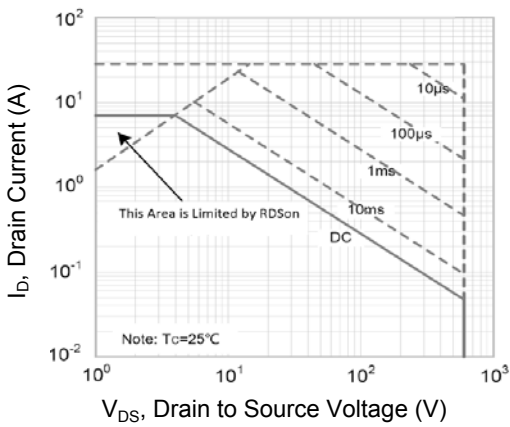
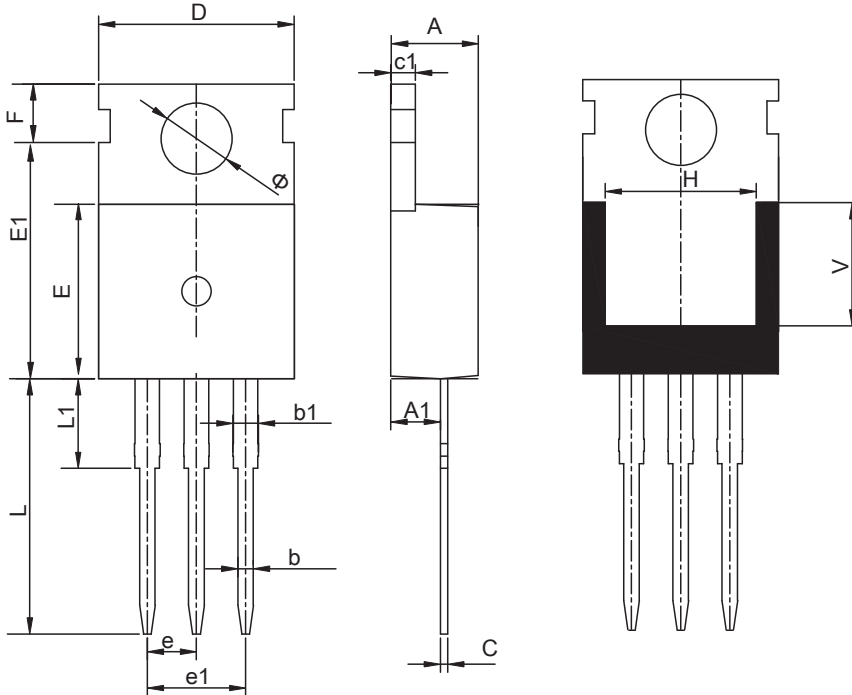


Figure 9. Safe Operation Area

Package Outline Dimensions (TO-220)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
A1	2.25	2.70	0.089	0.106
b	0.71	0.91	0.028	0.036
b1	1.17	1.37	0.046	0.054
C	0.33	0.65	0.013	0.026
c1	1.20	1.40	0.047	0.055
D	9.91	10.25	0.390	0.404
E	8.95	9.75	0.352	0.384
E1	12.65	13.00	0.498	0.512
e	2.54 TYP		0.100 TYP	
e1	4.98	5.18	0.196	0.204
F	2.65	2.95	0.104	0.116
H	7.90	8.10	0.311	0.319
L	12.90	13.40	0.508	0.528
L1	2.68	3.25	0.106	0.128
V	6.90 REF		0.272 REF	
Φ	3.40	3.80	0.134	0.150

Order Information

Device	Package	Marking	Carrier	Quantity
GSFH60R570	TO-220	H60R570	Tube	50pcs / Tube

For more information, please contact us at: inquiry@goodarksemi.com